IN THE CLAIMS:

Please cancel claims 3 and 11 and without prejudice, and amend the claims as follows:

1. (Currently Amended) A thermal shim adapted to be positioned between a wafer retention device and a pedestal, wherein said thermal shim comprises a disk having a thermally insulative material centrally located within a thermally conductive material.

2. (Canceled)

3. (Canceled)

4. (Previously Presented) The thermal shim of claim 1, wherein said thermally conductive material is in the shape of an annulus.

5. (Previously Presented) The thermal shim of claim 1, wherein the thermally conductive material is fabricated of a metallic material.

6. (Original) The thermal shim of claim 5 wherein said metallic material is aluminum or copper.

7. (Original) The thermal shim of claim 1 wherein the thermal shim is fabricated of a corrugated material.

8. (Canceled)

9. (Currently Amended) A wafer support comprising:

a heat exchanger pedestal having a top surface;

a thermal shim comprising a disk having a thermally insulative material centrally disposed within a thermally conductive material; and

a wafer retention device having a bottom surface, wherein the thermal shim is located between the bottom surface of the wafer retention device and the top surface of the heat exchanger pedestal.

10. (Canceled)

11. (Canceled)

12. (Previously Presented) The wafer support of claim 9, wherein said thermally conductive material is in the shape of an annulus.

13. (Previously Presented) The wafer support of claim 9, wherein the thermally conductive material is fabricated of a metallic material.

14. (Original) The wafer support of claim 13 wherein said metallic material is aluminum or copper.

15. (Original) The wafer support of claim 9 wherein the thermal shim is fabricated of a corrugated material.

16. (Canceled)

17. (Currently Amended) An etch reactor having a wafer support, wherein said wafer support comprises:

a heat exchanger pedestal having a top surface;

a thermal shim comprising a disk having a thermally insulative material centrally disposed within an annular shaped thermally conductive material; and

an electrostatic chuck having a bottom surface, wherein the thermal shim is located between the bottom surface of the electrostatic chuck and the top surface of the heat exchanger pedestal.

18. (Previously Presented) The etch reactor of claim 1, wherein the thermal shim is fabricated of metal.

19. (Previously Presented) The etch reactor of claim 1, wherein the thermal shim is corrugated.

20. (Currently Amended) A wafer support comprising:

a heat exchanger pedestal having a top surface;

means for controlling thermal conductivity comprising a disk having a thermally insulative material centrally disposed within a thermally conductive material; and

a wafer retention device having a bottom surface, wherein the means for controlling thermal conductivity is located between the bottom surface of the wafer retention device and the top surface of the heat exchanger pedestal.

21. (Original) The wafer support of claim 20 wherein said means for controlling the thermal conductivity is a thermal shim.

22. (Currently Amended) A thermal shim adapted to be positioned between a wafer retention device and a pedestal, wherein the thermal shim comprises a disk having a thermally conductive material centrally located within a thermally insulative material.

23. (Previously Presented) The thermal shim of claim 22, wherein the thermally insulative material is in the shape of an annulus.

24. (Previously Presented) The thermal shim of claim 22, wherein the thermally conductive material is fabricated of a metallic material.

25. (Previously Presented) The thermal shim of claim 24, wherein the metallic material is made from aluminum or copper.

26. (Currently Amended) A wafer support, comprising:

a heat exchanger pedestal having a top surface;

a thermal shim comprising a disk having a thermally conductive material centrally disposed within a thermally insulative material; and

a wafer retention device having a bottom surface, wherein the thermal shim is located between the bottom surface of the wafer retention device and the top surface of the heat exchanger pedestal.

27. (Previously Presented) The wafer support of claim 26, wherein the thermally insulative material is in the shape of an annulus.

28. (Previously Presented) The wafer support of claim 26, wherein the thermally conductive material is fabricated of a metallic material.

29. (Previously Presented) The wafer support of claim 26, wherein the metallic material is made from aluminum or copper.

30. (New) The thermal shim of claim 1, wherein the disk substantially covers a top surface of the pedestal.

31. (New) A thermal shim configured to be disposed between a substrate retention device and a pedestal, wherein the thermal shim comprises a disk that substantially covers a top surface of the pedestal.

32. (New) The thermal shim of claim 31, wherein the disk is made of two materials.

33. (New) The thermal shim of claim 31, wherein the disk comprises a low thermally conductive material disposed within a high thermally conductive material.

34. (New) The thermal shim of claim 31, wherein the disk comprises a high thermally conductive material disposed within a low thermally conductive material.